

IN THE SPECIFICATION

Please amend the paragraph beginning at line 7, page 4, as follows:

--As shown in Figures 2 and 3, a varactor 10 is formed on a silicon-on-insulation (SOI) structure 12 having a silicon layer 14 formed over an insulation layer 16. The insulation layer 16 may be formed of an oxide such as  $\text{SiO}_2$  and, as shown in Figure 3 2, is formed over a handle wafer 18. Silicon having a high resistivity may be used for the handle wafer 18. A plurality of MOS transistors is used to construct the varactor 10. A cross-sectional side view of one such transistor 20 is shown in Figure 3.--